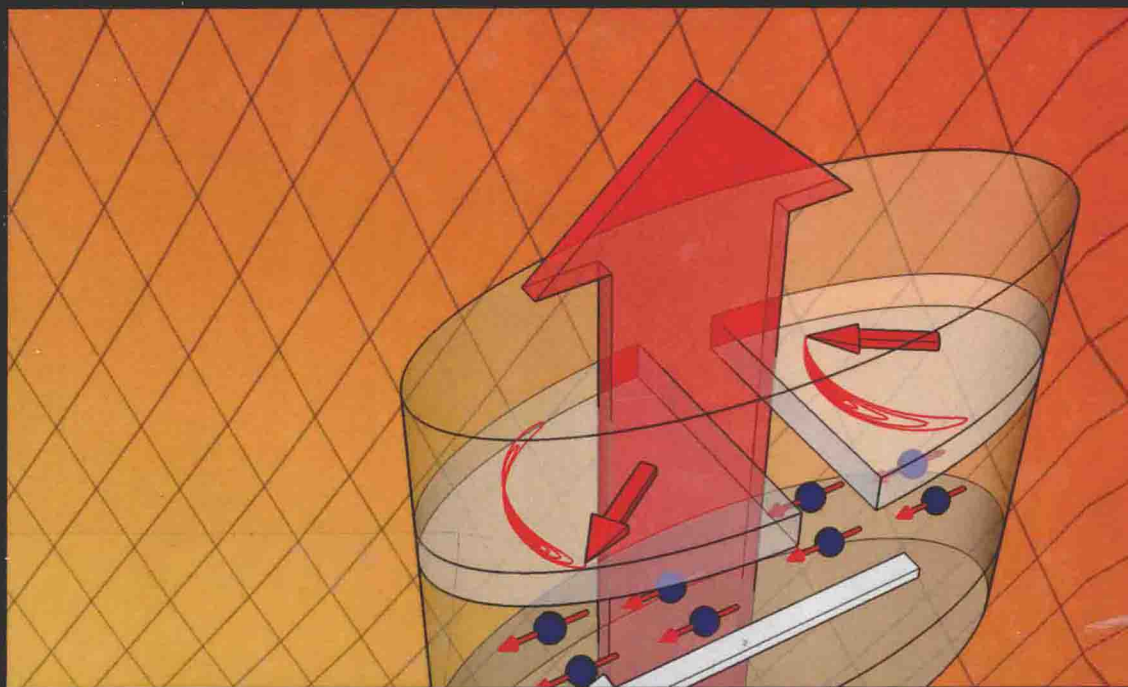


Future Trends in Microelectronics

Frontiers and Innovations

Serge Luryi • Jimmy Xu • Alex Zaslavsky



FUTURE TRENDS IN MICROELECTRONICS

Frontiers and Innovations

Edited by

SERGE LURYI

JIMMY XU

ALEX ZASLAVSKY



WILEY

Copyright © 2013 by John Wiley & Sons, Inc. All rights reserved.

Published by John Wiley & Sons, Inc., Hoboken, New Jersey.

Published simultaneously in Canada.

No part of this publication may be reproduced, stored in a retrieval system, or transmitted in any form or by any means, electronic, mechanical, photocopying, recording, scanning, or otherwise, except as permitted under Section 107 or 108 of the 1976 United States Copyright Act, without either the prior written permission of the Publisher, or authorization through payment of the appropriate per-copy fee to the Copyright Clearance Center, Inc., 222 Rosewood Drive, Danvers, MA 01923, (978) 750-8400, fax (978) 750-4470, or on the web at www.copyright.com. Requests to the Publisher for permission should be addressed to the Permissions Department, John Wiley & Sons, Inc., 111 River Street, Hoboken, NJ 07030, (201) 748-6011, fax (201) 748-6008, or online at <http://www.wiley.com/go/permission>.

Limit of Liability/Disclaimer of Warranty: While the publisher and author have used their best efforts in preparing this book, they make no representations or warranties with respect to the accuracy or completeness of the contents of this book and specifically disclaim any implied warranties of merchantability or fitness for a particular purpose. No warranty may be created or extended by sales representatives or written sales materials. The advice and strategies contained herein may not be suitable for your situation. You should consult with a professional where appropriate. Neither the publisher nor author shall be liable for any loss of profit or any other commercial damages, including but not limited to special, incidental, consequential, or other damages.

For general information on our other products and services or for technical support, please contact our Customer Care Department within the United States at (800) 762-2974, outside the United States at (317) 572-3993 or fax (317) 572-4002.

Wiley also publishes its books in a variety of electronic formats. Some content that appears in print may not be available in electronic format. For information about Wiley products, visit our web site at www.wiley.com.

Library of Congress Cataloging-in-Publication Data is available.

ISBN 978-1118-44216-6

Printed in the United States of America.

10 9 8 7 6 5 4 3 2 1

FUTURE TRENDS IN MICROELECTRONICS

Preface

S. Luryi

Dept. of Electrical and Computer Engineering

State University of New York, Stony Brook, NY 11794-2350, U.S.A.

J. M. Xu and A. Zaslavsky

School of Engineering, Brown University, Providence, RI 02912, U.S.A.

This book is a brainchild of the seventh workshop in the *Future Trends in Microelectronics* series (FTM-7). The first of the FTM conferences, "*Reflections on the Road to Nanotechnology*", had gathered in 1995 on Ile de Bendor, a beautiful little French Mediterranean island.¹ The second FTM, "*Off the Beaten Path*", took place in 1998 on a larger island in the same area, Ile des Embiez.² Instead of going to a still larger island, the third FTM, "*The Nano Millennium*", went back to its origins on Ile de Bendor in 2001.³ As if to compensate for small size of Bendor, the fourth FTM, "*The Nano, the Giga, the Ultra, and the Bio*", took place on the biggest French Mediterranean island of them all, Corsica.⁴ Normally, the FTM workshops gather every three years; however, the FTM-4 was held one year ahead of the usual schedule, in the summer of 2003, as a one-time exception. Continuing its inexorable motion eastward, the fifth FTM workshop, "*Up the Nano Creek*", had convened on Crete, Greece, in June of 2006.⁵ The inexorable motion was then interrupted to produce a semblance of a random walk in the Mediterranean and the FTM-6 "*Unmapped Roads*" went to the Italian island of Sardinia (June, 2009).⁶ The last FTM gathering, "*Into the Cross Currents*", returned to our earlier venue on Corsica (June 2012).

The FTM workshops are relatively small gatherings (less than 100 people) by invitation only. If you, the reader, wish to be invited, please consider following a few simple steps outlined on the conference website. The FTM website at www.ece.sunysb.edu/~serge/FTM.html contains links to all past and planned workshops, their programs, publications, sponsors, and participants. Our attendees have been an illustrious lot. Suffice it to say that among FTM participants we find five Nobel laureates (Zhores Alferov, Herbert Kroemer, Horst Stormer, Klaus von Klitzing, and Harold Kroto) and countless others poised for a similar distinction. To be sure, high distinction is not a prerequisite for being invited to FTM, but the ability and desire to bring fresh ideas is. All participants of FTM-7 can be considered authors of this book, which in this sense is a collective treatise.

The main purpose of FTM workshops is to provide a forum for a free-spirited exchange of views, projections, and critiques of current and future directions, among the leading professionals in industry, academia, and government.

For better or worse our civilization is destined to be based on electronics. Ever since the invention of the transistor and especially after the advent of integrated circuits, semiconductor devices have kept expanding their role in our lives. Electronic circuits entertain us and keep track of our money, they fight our wars and decipher the secret codes of life, and one day, perhaps, they will relieve us from the burden of thinking and making responsible decisions. Inasmuch as that day has not yet arrived, we have to fend for ourselves. The key to success is to have a clear vision of where we are heading. In the blinding light of a bright future, the FTM community has remained mindful of the fact that what controlled the past will still control the future – the basic principles of science. Thus, the trendy, red-hot projections of any given epoch deserve and require critical scrutiny.

Some degree of stability is of importance in these turbulent times and should be welcome. Thus, although the very term "*microelectronics*" has been generally re-christened "*nanoelectronics*", we have stuck to the original title of the FTM workshop series.

The present volume contains a number of original papers, some of which were presented at FTM-7 in oral sessions, other as posters. From the point of view of the program committee, there is no difference between these types of contributions in weight or importance. There was, however, a difference in style and focus – and that was intentionally imposed by the organizers. All speakers were asked to focus on the presenter's views and projections of future directions, assessments or critiques of important new ideas/approaches, and *not* on their own achievements. This latter point is perhaps the most distinctive feature of FTM workshops. Indeed, we are asking scientists not to speak of their own work! This has proven to be successful, however, in eliciting powerful and frank exchange. The presenters are asked to be provocative and/or inspiring. Latest advances made and results obtained by the participants are to be presented in the form of posters and group discussions.

Each day of the workshop was concluded by an evening panel or poster session that attempted to further the debates on selected controversial issues connected to the theme of the day. Each such session was chaired by a moderator who invited two or three attendees of his or her choice to lead with a position statement, with all other attendees serving as panelists. The debate was forcefully moderated and irrelevant digressions cut off without mercy. Moderators were also assigned the hopeless task of forging a consensus on critical issues.

To accommodate these principles, the FTM takes a format that is less rigid than usual workshops to allow and encourage uninhibited exchanges and sometimes confrontations of different views. A central theme is designed together with the speakers for each day. Another traditional feature of FTM workshops is a highly informal vote by the participants on the relative importance of various fashionable current topics in modern electronics research. This tradition owes its origin to Horst Stormer, who composed the original set of questions and maintained the results over four conferences. These votes are perhaps too bold and irreverent for general publication, but they are carefully maintained and made

available to every new generation of FTM participants. Another traditional vote concerned the best poster. The 2012 winning poster was "Mechanical energy harvesting with piezoelectric nanostructures: Great expectations for autonomous systems" by Gustavo Ardila.

A joyful tradition of FTM meetings is the settling of scientific bets, a custom that dates back to the 1998 wager between Nikolai Ledentsov (pro) and Horst Stormer (con) about the putative future dominance of quantum dot-based lasers – a bet that Horst collected in 2004, at FTM-4. Another risky bet on the future dominance of SOI technology is to be adjudicated at a future (2015) workshop. The precise statement of this "good" bet (worth a six-magnum case of very good champagne) is: by 2015, SOI will cover more than 35% of the CMOS market including memories by value. This bet, proposed by Sorin Cristoloveanu, attracted three cons – Detlev Grützmacher, Dimitris Ioannou, and Enrico Sangiorgi – who will have to divide the spoils, should SOI fail to reach the mark. Several "bad" (penniless) bets that were supposed to be resolved at FTM-7 were put off as premature by the principals. Hopefully, by 2015 it will become clear whether or not "10% of all man-produced light will be white LED" (Michael Shur), "we shall have hi-fi real-time pocket translators" (Hiroshi Iwai), "most cars will have IP addresses" (Jimmy Xu), or "the Si industry will no longer be recognizable and there will be (essentially) no further improvement in devices" (Paul Solomon).

Not every contribution presented at FTM-7 has made it into this book (not for the lack of persistence by the editors). Perhaps most sorely we miss the exciting contribution by David Miller of Stanford University, entitled "The heat death of information processing and why interconnects matter more than logic", in which he illustrated how the energy required by data communication is imposing severe limits on overall information processing, with the demand for communications bandwidth increasing a hundredfold every decade. As a result, he posited very low energy optoelectronics densely integrated with logic as a way of allowing the continued scaling of information processing systems. Abstracts of his and all other presentations can be found on the program webpage, <http://www.ee.sunysb.edu/~serge/ARW-7/program.html>

The FTM meetings are known for the professional critiques – or even demolitions – of fashionable trends, that some may characterize as hype. The previous workshops had witnessed powerful assaults on quantum computing, molecular electronics, and spintronics. This time Michel Dyakonov offered another thorough and conclusive update on quantum computing. It seems that by now most of the hype associated with some of these trends has dissipated and perhaps we can take some credit for the more balanced outlook that has emerged since.

We have grouped all contributions into four chapters: one dealing with transistors and CMOS or CMOS-compatible technology, another with photonics and lasers, and still another with solar cell and energy harvesting. The last chapter collected the contributions focused on fundamental physics and other, less

technological subjects. The breakdown could not be uniquely defined, because some papers fit two or even three categories!

To produce a coherent collective treatise out of all of this, the interaction between FTM participants had begun well before their gathering at the workshop. All the proposed presentations were posted on the web in advance and could be subject to change up to the last minute to take into account peer criticism and suggestions. After the workshop is over, these materials (not all of which have made it into this book) remain on the web indefinitely, and the reader can peruse them starting at the www.ece.sunysb.edu/~serge/FTM.html home page.

Acknowledgments

The 2012 FTM workshop on Corsica and therefore this book were possible owing to support from:

- US National Science Foundation
- U.S. Department of Defense: ARO
- U.S. DoD European offices: EOARD, ONR–Global
- Industry: SAIT, Samsung Electronics Co.
- Academia: SUNY–Stony Brook, Brown University.

On behalf of all workshop attendees sincere gratitude is expressed to the above organizations for their generous support and especially to the following individuals whose initiative was indispensable: William Clark, John Gonglewski, Kinam Kim, Mark Pinto, Shawn Thorne, Robert True, and John Zavada.

Finally, the organizers wish to thank all of the contributors to this volume and all the attendees for making the workshop a rousing success.

References

1. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: Reflections on the Road to Nanotechnology*, NATO ASI Series E Vol. 323, Dordrecht: Kluwer Academic, 1996.
2. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: The Road Ahead*, New York: Wiley Interscience, 1999.
3. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: The Nano Millennium*, New York: Wiley Interscience/IEEE Press, 2002.
4. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: The Nano, The Giga, and The Ultra*, New York: Wiley Interscience/IEEE Press, 2004.
5. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: Up the Nano Creek*, Hoboken, NJ: Wiley Interscience/IEEE Press, 2007.
6. S. Luryi, J. M. Xu, and A. Zaslavsky, eds., *Future Trends in Microelectronics: From Nanophotonics to Sensors to Energy*, Hoboken, NJ: Wiley Interscience/IEEE Press, 2010.

CONTENTS

Preface

S. Luryi, J. M. Xu, and A. Zaslavsky ix

I INNOVATIONS IN ELECTRONICS AND SYSTEMS 1

Technology Innovation, Reshaping the Microelectronics Industry 4

K. Kim and U.-I. Chung

Challenges and Limits for Very Low Energy Computation 49

F. Balestra

Getting Rid of the DRAM Capacitor 59

N. Rodriguez, F. Gamiz, and S. Cristoloveanu

Physics and Design of Nanoscale Field Effect Diodes for Memory and ESD Protection Applications 73

D. E. Ioannou, Z. Chbili, A. Z. Badwan, Q. Li, Y. Yang, and A. A. Salman

Sharp-Switching CMOS-Compatible Devices with High Current Drive 81

J. Wan, S. Cristoloveanu, S. T. Le, A. Zaslavsky, C. Le Royer, S. A. Dayeh, D. E. Perea, and S. T. Picraux

Magnetic Tunnel Junctions with a Composite Free Layer: A New Concept for Future Universal Memory 93

A. Makarov, V. Sverdlov, and S. Selberherr

Silicon Carbide High Temperature Electronics – Is This Rocket Science? 102

C.-M. Zetterling

Microchip Post-Processing: There is Plenty of Room at the Top 110

J. Schmitz

EUV Lithography: Today and Tomorrow 120

V. Y. Banine

Manufacturability and Nanoelectronic Performance 133

M. J. Kelly

II OPTOELECTRONICS IN THE NANO AGE	139
Ultrafast Nanophotonic Devices For Optical Interconnects	142
<i>N. N. Ledentsov, V. A. Shchukin, and J. A. Lott</i>	
Will Optical Communications Meet the Challenges of the Future?	160
<i>D. K. Mynbaev</i>	
Optical Antennae for Optoelectronics: Impacts, Promises, and Limitations	173
<i>H. Mohseni</i>	
Spin Modulation: Teaching Lasers New Tricks	183
<i>J. Lee, G. Bo��ris, R. Oszwa��dowski, K. V��born��y, C. G��thgen, and I. ��uti��</i>	
 III HARVESTING ENERGY FROM THE SUN AND THE ENVIRONMENT	 191
Silicon Photovoltaics: Accelerating to Grid Parity	194
<i>M. R. Pinto</i>	
Two- and Three-Dimensional Numerical Simulation of Advanced Silicon Solar Cells	210
<i>E. Sangiorgi, M. Zanucoli, R. De Rose, P. Magnone, and C. Fiegna</i>	
Mechanical Energy Harvesting with Piezoelectric Nanostructures: Great Expectations for Autonomous Systems	230
<i>G. Ardila, R. Hinchet, L. Mont��s, and M. Mouis</i>	
Charged Quantum Dots for Photovoltaic Conversion and IR Sensing	244
<i>A. Sergeev, V. Mitin, N. Vagidov, and K. Sablon</i>	
Active Optomechanical Resonators	254
<i>D. Princepe, L. Barea, G. O. Luiz, G. Wiederhecker, and N. C. Frateschi</i>	

IV PHYSICS FRONTIERS	263
State of the Art and Prospects for Quantum Computing <i>M. I. Dyakonov</i>	266
Wireless, Implantable Neuroprosthesis: Applying Advanced Technology to Untether the Mind <i>D. A. Borton and A. V. Nurmikko</i>	286
Correlated Electrons: A Platform for Solid State Devices <i>S. D. Ha, Y. Zhou, R. Jaramillo, and S. Ramanathan</i>	300
Graphene-Based Integrated Electronic, Photonic and Spintronic Circuit <i>A. D. Güçlü, P. Potasz, and P. Hawrylak</i>	308
Luttinger Liquid Behavior of Long GaAs Quantum Wires <i>E. Levy, I. Sternfeld, M. Eshkol, M. Karpovski, A. Palevski, B. Dwir, A. Rudra, E. Kapon, and Y. Oreg</i>	319
Toward Spin Electronic Devices Based on Semiconductor Nanowires <i>S. Heedt, I. Wehrmann, K. Weis, H. Hardtdegen, D. Grützmacher, Th. Schäpers, C. Morgan, D. E. Bürgler, and R. Calarco</i>	328
An Alternative Path for the Fabrication of Self-Assembled III-Nitride Nanowires <i>A. Haab, M. Mikulics, T. Stoica, B. Kardynal, A. Winden, H. Hardtdegen, D. Grützmacher, and E. Sutter</i>	340
InAs Nanowires with Surface States as Building Blocks for Tube-Like Electrical Sensing Transistors <i>N. V. Demarina, M. I. Lepsa, and D. Grützmacher</i>	351
Lévy Flight of Photoexcited Minority Carriers in Moderately Doped Semiconductors: Theory and Observation <i>A. Subashiev and S. Luryi</i>	359
Terahertz Plasma Oscillations in Field Effect Transistors: Main Ideas and Experimental Facts <i>W. Knap and M. I. Dyakonov</i>	373
INDEX	395

Part I

Innovations in Electronics and Systems

I. Innovations in Electronics and Systems

The incredibly powerful silicon electronics is still full of steam, charging ahead despite the putatively insurmountable barriers and walls (of thermal, power, wiring, and scaling, for example). Equally evident is that the challenges ahead are real, getting greater, and often without a clear answer. One example is transition to EUV lithography, discussed in the chapter by Banine. What are the biggest challenges anticipated and the biggest changes assumed in the existing roadmap? If science is not (yet) the ultimate limit to nanoelectronics, is it manufacturability, discussed in the chapter by Kelly? What are the most desired innovations, and the most disruptive, interesting, and controversial directions? While the drive for ever greater device performance – discussed in a number of chapters devoted to novel memory and logic devices – is becoming prohibitively costly, could the advances in systems and integrated functionalities be sufficiently rewarding to justify and become the next driving force? These questions are addressed in Part I of this book, which opens with an insightful and comprehensive discussion of technology innovation by Kim and Chung, from the innovation powerhouse of Samsung Electronics.

Contributors

- 1.1 K. Kim and U-I. Chung
- 1.2 F. Balestra
- 1.3 N. Rodriguez, F. Gamiz, and S. Cristoloveanu
- 1.4 D. E. Ioannou, Z. Chbili, A. Z. Badwan, Q. Li, Y. Yang, and A. A. Salman
- 1.5 J. Wan, S. Cristoloveanu, S. T. Le, A. Zaslavsky, C. Le Royer, S. A. Dayeh, D. E. Perea, and S. T. Picraux
- 1.6 A. Makarov, V. Sverdlov, and S. Selberherr
- 1.7 C.-M. Zetterling
- 1.8 J. Schmitz
- 1.9 V. Y. Banine
- 1.10 M. J. Kelly

Technology Innovation, Reshaping the Microelectronics Industry

Kinam Kim and U-In Chung

*Samsung Advanced Institute of Technology, Samsung Electronics Co. Ltd.
Giheung, Gyeonggi-do, South Korea*

1. Introduction

The remarkable evolution of electronics was enabled by the rapidly advancing silicon technology. The performance of such devices as CPUs and memories has improved tremendously over the past 20 years: CPUs improved by a factor of 2,400, DRAM by a factor of 1,000 and NAND Flash by a factor of 32,000. Mobile network speed has also increased by a factor of 840, stimulated by an increased usage of smartphones and tablets, which have grown by 58%¹ and 260%² in 2011, respectively. Furthermore, Internet communication traffic is anticipated to increase by 32% annually, with the traffic reaching an order of zeta (10^{21}) bytes by 2015.³

These performance improvements have been made possible by silicon technology downscaling, which is nearing the 20 nm node and will soon reach 10 nm. Novel fabrication techniques, structures and materials will be required to continue scaling beyond 10 nm to satisfy the data handling, processing and storage requirements of the future.

Future device development will be constrained by power consumption, in addition to the traditional scaling issues, since faster and higher data handling and processing will unavoidably require a lot of power. For instance, 1.1 petaflop (10^{15}) computing in 2008⁴ consumed 2.3 MW power for its operation, so an exascale (10^{18}) system might dissipate an estimated 2.3 GW, roughly equivalent to the electricity produced by two nuclear power plants. Most of this energy is lost in the inefficient metal interconnects, which could be reduced by combining photonics with Si technologies. This silicon-photonics convergence will create new applications and markets in the future.

Furthermore, silicon technology is bringing innovation to new areas, such as energy, health, and medical applications. Examples of this are ultrafast DNA sequencing, extremely compact and efficient medical imaging devices, and low-cost energy-efficient lighting, among others. These applications, fueled by Si technologies, could eventually take up a major portion of the semiconductor market in the next decade.

2. Mainstream silicon technology: Memory

- *Towards sub-20 nm DRAM*

DRAM density has doubled every 18 months through scaling of the critical dimensions, approaching the 20 nm node today, as shown in Fig. 1. Major challenges to downscaling to the sub-10 nm regime will require device innovations in cell storage capacitors, cell array transistors (CATs) and patterning processes.⁵

The minimum cell capacitance must be maintained to provide an adequate signal for sensing and to meet retention time specifications.⁶ In order to maintain the cell capacitance, as DRAM downscaled from 90 nm to 20 nm, the capacitor structure has been changed from a simple 3D cylindrical shape to an extremely high aspect ratio (AR) supported cylinder or pillar structure, as shown in Fig. 2. For sub-10 nm DRAMs, structural innovation may not help any longer due to physical limitations in accommodating complex 3D structures. At sub-10 nm nodes, the distance between electrodes becomes ~10 nm or less, which in turn requires the physical thickness of the storage electrodes and the dielectrics to be thinner than 5 nm or less. These requirements will be very difficult to meet. However, the limitation of cell capacitance can be compensated by the technological innovation in CAT with extremely low leakage currents and/or array architecture and its integration process to provide high sensing signals.

From a device point of view, requirements related to the retention limit can be overcome by suppressing the storage node leakage current I_{LEAK} . The data retention time t_{RE} is fundamentally determined by the amount of the stored charge and the time-dependent charge loss at the storage node.⁷ The sensing voltage ΔV_{BL} is as follows:

$$\Delta V_{BL} = \frac{C_S}{C_{BL} + C_S} \left(\frac{V_{ARR}}{2} - \Delta V_L \right), \quad (1)$$

where C_S is the cell storage capacitance, V_{ARR} is the array voltage, C_{BL} is the bit

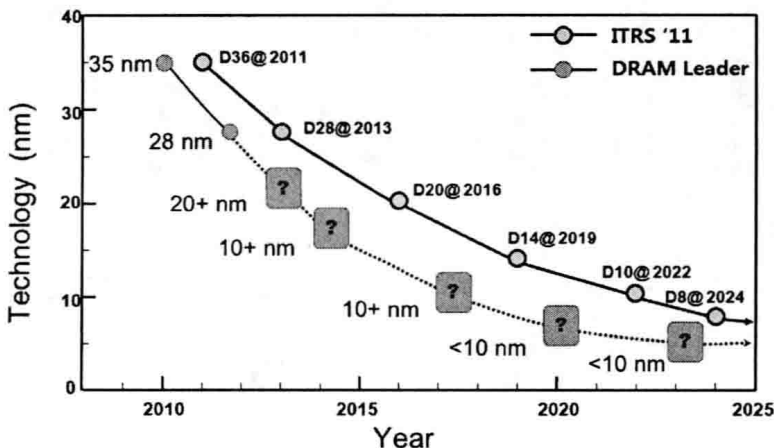


Figure 1. DRAM technology roadmap of ITRS and top DRAM supplier.